**Product data sheet** 

## 1. General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

#### 2. Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for logic level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

## 3. Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching
- · Motors, lamps and solenoids

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	55	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u> ; <u>Fig. 3</u>	[1]	-	-	62	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	115	W
Static charact	eristics				1		
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C		-	11	13.6	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C		-	-	16.6	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11; Fig. 12		-	13	15	mΩ
Dynamic char	acteristics						
$Q_{GD}$	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 25 \text{ A}; V_{DS} = 44 \text{ V};$ $T_j = 25 \text{ °C}; Fig. 9$		-	20	-	nC



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							
E <sub>DS(AL)</sub> S	non-repetitive drain- source avalanche energy	$I_D$ = 62 A; $V_{sup} \le$ 55 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	-	211	mJ

[1] Current is limited by power dissipation chip rating.

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D 1
2	D	drain		
3	S	source	\\\\	G-VI-4
mb	D	mounting base; connected to drain	1 3 DPAK (SOT428)	mbb076 S

## 6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK9215-55A	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428		

## 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	55	V
$V_{DGR}$	drain-gate voltage	$R_{GS}$ = 20 k $\Omega$		-	55	V
V <sub>GS</sub>	gate-source voltage			-15	15	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	115	W
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2</u> ; <u>Fig. 3</u>	[1]	-	62	Α
			<u>[2]</u>	-	55	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 5 V; <u>Fig. 2</u>	[1]	-	44	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 3		-	248	Α
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	in diode		'	'		
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[2]	-	55	Α
			[1]	-	62	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	248	Α
Avalanche i	ruggedness			'		,
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 62 A; $V_{sup} \le$ 55 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; unclamped		-	211	mJ

<sup>[1]</sup> Current is limited by power dissipation chip rating.

<sup>[2]</sup> Continious current is limited by bond wires.

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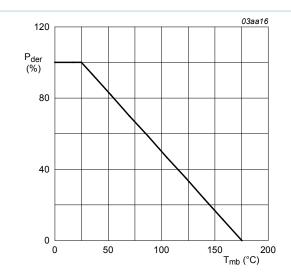


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{\textit{der}} = \frac{P_{\textit{tot}}}{P_{\textit{tot}(25^{\circ}\textit{C})}} \times \textbf{100 \%}$$

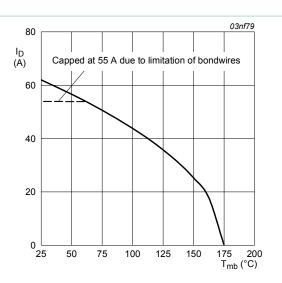


Fig. 2. Continuous drain current as a function of mounting base temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

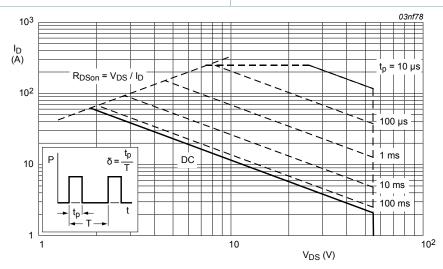


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25$ °C;  $I_{DM}$  is single pulse

N-channel TrenchMOS logic level FET

## 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	-	1.3	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		-	71.4	-	K/W

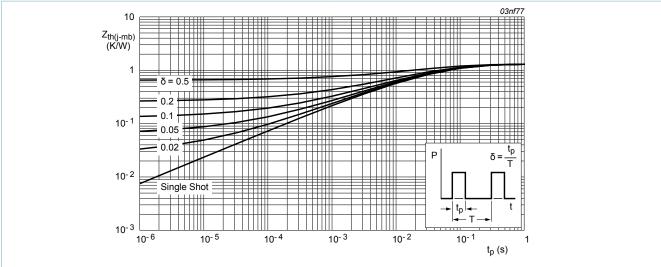


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

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## 9. Characteristics

#### Table 6 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	55	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = -55 °C; Fig. 10	-	-	2.3	V
		$I_D$ = 1 mA; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 175 °C; Fig. 10	0.5	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 10	1	1.5	2	V
I <sub>DSS</sub> drain	drain leakage current	V <sub>DS</sub> = 55 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.05	10	μA
		V <sub>DS</sub> = 55 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	11	13.6	mΩ
resista	resistance	V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C	-	-	16.6	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 11; Fig. 12	-	-	30	mΩ
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11; Fig. 12	-	13	15	mΩ
Dynamic cl	haracteristics		'			
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 44 V; V <sub>GS</sub> = 5 V;	-	48	-	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	6	-	nC
$Q_{GD}$	gate-drain charge		-	20	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	2190	2916	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 13</u>	-	380	450	pF
C <sub>rss</sub>	reverse transfer capacitance		-	250	344	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; $R_L$ = 1.2 $\Omega$ ; $V_{GS}$ = 5 V;	-	19	-	ns
t <sub>r</sub>	rise time $R_{G(ext)} = 10 \Omega; T_j = 25 °C$	$R_{G(ext)}$ = 10 Ω; $T_j$ = 25 °C	-	161	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	138	-	ns
t <sub>f</sub>	fall time		-	165	-	ns
L <sub>D</sub>	internal drain inductance	measured from drain to centre of die	-	2.5	-	nH

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
L <sub>S</sub>	internal source inductance	measured from source lead to source bond pad		-	7.5	-	nH
Source-drain diode							
V <sub>SD</sub>	source-drain voltage	$I_S = 20 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 14$		-	0.85	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$		-	51	-	ns
Q <sub>r</sub>	recovered charge	$V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$		-	102	-	nC

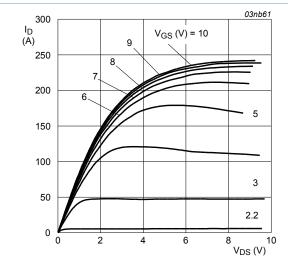


Fig. 5. Output characteristics: drain current as a function of drain-source voltage; typical values



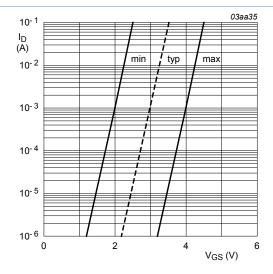


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25\,^{\circ}C; V_{DS} = 5V$$

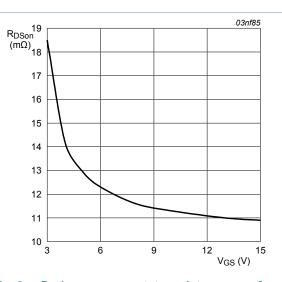


Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

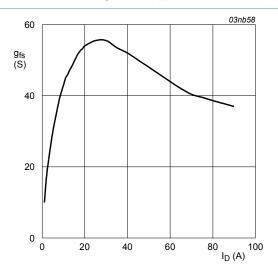


Fig. 8. Forward transconductance as a function of drain current; typical values

$$T_j=25^{\circ}C; V_{DS}=25V$$

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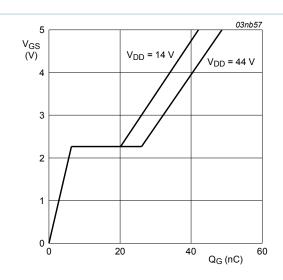


Fig. 9. Gate-source voltage as a function of turn-on gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

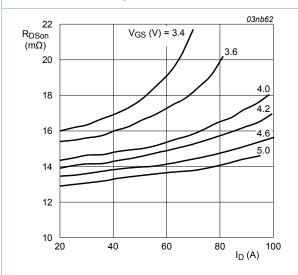


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^{\circ}C$$

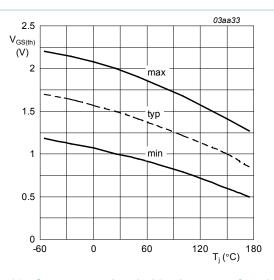


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1mA; V_{DS} = V_{GS}$$

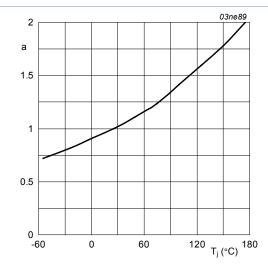


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

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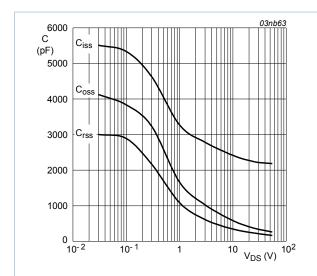
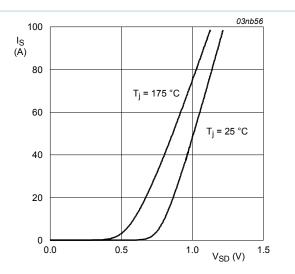


Fig. 13. Input, output and reverse transfer capacitances Fig. 14. Reverse diode current; typical value as a function of drain-source voltage; typical values

$$V_{GS} = 0V; f = 1MHz$$



$$V_{\it GS} = 0V$$

## 10. Package outline

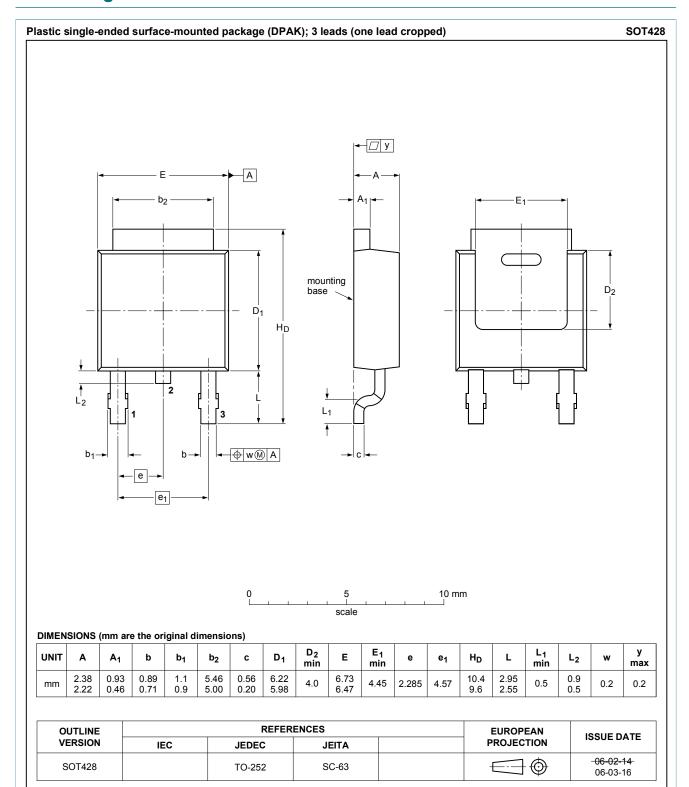


Fig. 15. Package outline DPAK (SOT428)

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